

isc Silicon NPN Power Transistor

2SC937

DESCRIPTION

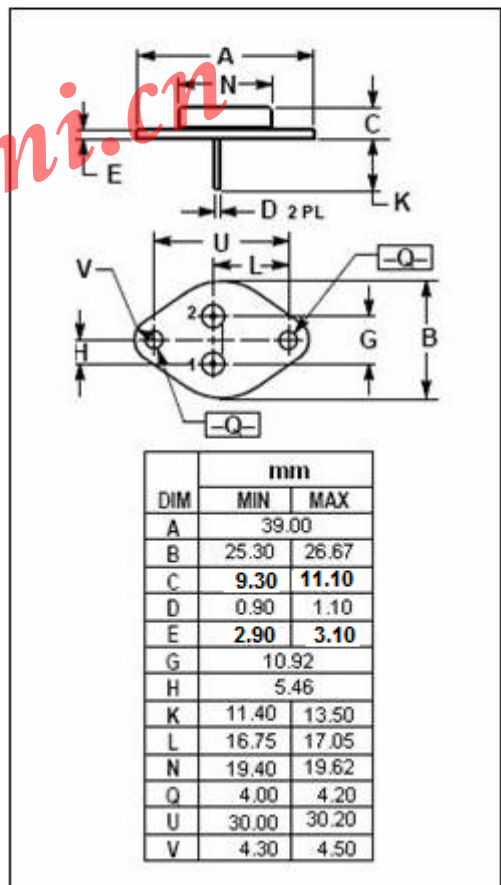
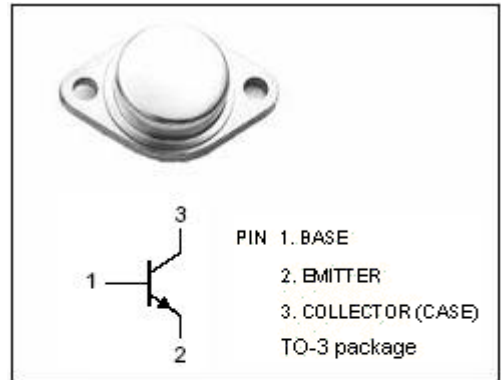
- High Breakdown Voltage-  
:  $V_{CBO}=1200V(\text{Min})$
- High Reliability

APPLICATIONS

- Designed for TV horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER   | VALUE   | UNIT             |
|-----------|---|---------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                                  | 1200    | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                               | 500     | V                |
| $V_{EBO}$ | Emitter-Base Voltage                                    | 6       | V                |
| $I_C$     | Collector Current- Continuous                           | 2.5     | A                |
| $I_{CP}$  | Collector Current-Pulse                                 | 6       | A                |
| $P_C$     | Collector Power Dissipation<br>@ $T_C=25^\circ\text{C}$ | 22      | W                |
| $T_J$     | Junction Temperature                                    | 125     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                               | -45~125 | $^\circ\text{C}$ |



**isc Silicon NPN Power Transistor****2SC937****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS   | MIN | TYP. | MAX | UNIT          |
|---------------|--------------------------------------|--|-----|------|-----|---------------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage  | $I_C=10\text{mA}; R_{BE}=\infty$   | 500 |      |     | V             |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C=2.5\text{A}; I_B=0.8\text{A}$   |     |      | 5.0 | V             |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage      | $I_C=2.5\text{A}; I_B=0.8\text{A}$   |     |      | 1.8 | V             |
| $I_{CBX}$     | Collector Cutoff Current             | $V_{CB}=1200\text{V}; V_{EB}=1.5\text{V}$                                    |     |      | 1   | mA            |
| $I_{EBO}$     | Emitter Cutoff Current               | $V_{EB}=6\text{V}; I_C=0$  |     |      | 0.2 | mA            |
| $t_f$         | Fall Time                            | $I_C=2.5\text{A}, I_{B1}=0.8\text{A}, I_{B2}=-1\text{mA}; L_B=10\mu\text{H}$ |     |      | 1.2 | $\mu\text{s}$ |

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